

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	23	(electron near5 beam) same (etch\$4 with polymer\$4 with pattern\$4) same (molecular nano\$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:05
S5	1906	b23k015\$.ipc.	JPO	OR	ON	2005/08/31 13:08
S6	78230	(nano\$9 molecu\$5) and etch\$4 and (polymer\$4 pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:11
S7	1	S6 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:10
S8	675457	(nano\$9 molecu\$5) and (polymer\$4 pattern\$4) not S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:11
S9	1	S8 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:28
S10	0	S5 and (sacric\$7 with layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:29
S11	0	S5 and sacric\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:29
S12	0	S5 and (sacrific\$4 with layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:30
S13	0	S5 and sacrific\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:30

S14	1906	S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:30
S15	1	S5 and (etch\$5 and (organic molecul\$3) and conduct\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:33
S16	5506	adsorb\$ with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:33
S17	422	adsorb\$ with electrode with molecul\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:34
S18	7	(adsorb\$ with electrode with molecul\$5) and ((remov\$5 with sacrific\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:41
S19	1	(adsorb\$ with electrode with molecul\$5) and ((remov\$5 with sacrific\$5) same (eb electron beam radiation laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:37
S20	1	("6306740").PNL	USPAT; USOCR	OR	OFF	2005/08/31 13:37
S21	72	(adsorb\$ with electrode with molecul\$5) and ((remov\$5 sacrific\$5) with layer\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:22
S22	189	204/486.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:23
S23	618	205/122.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:23
S24	2583	216/2,39,40,56,66,72.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:23

S25	2637	313/504.cds.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:24
S26	1438	438/48,99.cds.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:24
S27	2597	250/492.3.cds.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:24
S28	10014	S22 S23 S24 S25 S26 S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:24
S29	1618	S28 and (conduct\$4 with organic\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:25
S30	601	S28 and ((conduct\$4 with organic\$5) with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:25
S31	670	S28 and ((conduct\$4 with organic\$5) with (electrode pattern\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:26
S32	139	S31 and (nano nano\$15)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:30
S33	45	S32 and ((remov\$4 etch\$5) with (pattern\$5 trace polymer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 06:26
S34	12	S32 and (((remov\$4 etch\$5) with (pattern\$5 trace polymer)) and ((remov\$4 etch\$5) with (electron beam laser)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 05:50
S35	1	("5409783").PN.	USPAT; USOCR	OR	OFF	2005/09/01 05:50
S36	33946	c08j005\$.ipc.	JPO	OR	ON	2005/09/01 06:40

S37	125742	g02f001\$.ipc.	JPO	OR	ON	2005/09/01 06:41
S38	158907	S36 S37	JPO	OR	ON	2005/09/01 06:41
S39	0	S38 and electrode and sacrific \$5 and organic and conduct\$5	JPO	OR	ON	2005/09/01 06:59
S40	1	S38 and electrode and sacrific \$5 and organic	JPO	OR	ON	2005/09/01 06:43
S41	3	S38 and sacrific\$5 and organic	JPO	OR	ON	2005/09/01 06:43
S42	224	S38 and nano\$9	JPO	OR	ON	2005/09/01 06:43
S43	9	S38 and nano\$9 and gap	JPO	OR	ON	2005/09/01 06:43
S44	10	S38 and (bridge gap) and nano \$9	JPO	OR	ON	2005/09/01 07:01
S45	7	S38 and air and bridge	JPO	OR	ON	2005/09/01 07:01
S46	37	((electron near\$ beam) radiation) same (etch\$4 with polymer\$4 with pattern\$4) same (molecular nano\$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:23
S47	47	((electron near\$ beam) radiation laser) same (etch\$4 with polymer\$4 with pattern\$4) same (molecular nano\$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:25
S52	2	S47 and bridge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:27
S53	17	S47 and organic\$4 with (thin film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:27
S54	10	S47 and organic\$4 with thin with film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:29
S55	22	S47 and (organic\$4 thin film) with (electron beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:30
S58	0	S55 and (nanogap (nano adj gap) nano?gap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:32

S59	5	S55 and nano	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:34
S60	2	"20050051768"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:35
S61	1	S60 and passivat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:38
S62	3	"20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 10:58
S63	2	S62 and passivat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 10:38
S64	1	("5658698").PN.	USPAT; USOCR	OR	OFF	2006/09/09 11:14
S65	1	S64 and electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/09 11:14
S66	3	"20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 11:54
S67	3	S66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:22
S68	3	S67 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 11:55
S69	2	S67 and electrode with (resist\$4 insulat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 11:55

S70	2	S67 and electrode with (resist\$4 insulat\$4) with form\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 11:56
S71	2	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and sacrific\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 11:57
S72	2	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:01
S73	7	(organic near2 molecular) and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:00
S74	39	((organic near2 molecular) (micro adj scale) (nano adj scale)) and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:35
S75	0	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and photoetch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:01
S76	0	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and photo adj etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:02
S77	2	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:03
S78	0	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 and (pattern\$4 with (line width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:04
S79	0	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 and (pattern\$4 with polymer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:05
S80	2	S67 and (electrode with (resist\$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 and polymer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:05

S81	2	S67 and (electrode with (resist \$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 same polymer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:06
S82	2	S67 and (electrode with (resist \$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 same polymer and (electron with beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:15
S83	2	S67 and (electrode with (resist \$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 same polymer and (electron with beam) and pattern\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:16
S84	2	S67 and (electrode with (resist \$4 insulat\$4) with form\$4) and (sacrific\$9 with pattern\$4) and etch\$4 same polymer and (electron with beam) and (metal near3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:16
S85	18	S74 and (electron near3 beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:34
S86	29	((organic near2 molecular) (micro adj scale) (nano adj scale)) and (electrode with (resist\$4 insulat\$4) with form \$4) and ((sacrific\$9 polymer\$3) with pattern\$4 with (electron beam laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:01
S87	27	((organic near2 molecular) (micro adj scale) (nano adj scale)) and (electrode with (resist\$4 insulat\$4) with form \$4) and ((sacrific\$9 polymer\$3) with pattern\$4 with (electron laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:37
S88	11	((organic near2 molecular) (micro adj scale) (nano adj scale)) and (electrode with (resist\$4 insulat\$4) with form \$4) and ((sacrific\$9 polymer\$3) with (pattern\$4 remov\$4 ablat \$4) with ((electron laser) near2 beam))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:38
S89	57	(polymer\$4 near5 pattern\$4) with (line wide width dimension size) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:40

S90	1	S88 and S89	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:39
S91	8506	pattern\$4 with (line wide width dimension size) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:42
S92	57	S89 and S91	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:41
S93	2	S88 and S91	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:41
S94	72	pattern\$4 with (line wide width dimension size) with (nm nanometer) same ((laser electron) near5 beam) and ((organic molecular) near5 (device apparatus))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:56
S95	1	S88 and S94	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:56
S96	155	pattern\$4 with (line wide width dimension size) same (nm nanometer) same ((laser electron) near5 beam) and ((organic molecular) near5 (device apparatus))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:57
S97	1	S88 and S96	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:57
S98	128	pattern\$4 with (line wide width dimension size) same (organic molecular) same (nm nanometer) same ((laser electron) near5 beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:59
S99	0	S88 and S98	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:59

S100	2042	pattern\$4 with (line wide width dimension size) same (nm nanometer) same ((laser electron) near5 beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:59
S101	1	S88 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 12:59
S102	2381	pattern\$4 same (line wide width dimension size) with (nm nanometer) same ((laser electron) with beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:00
S103	1	S88 and S102	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:00
S104	9312	(line wide width dimension size) with (nm nanometer) same ((laser electron) with beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:01
S105	1	S88 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:00
S106	1	S86 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:01
S107	1	S74 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:01
S108	448	(line wide width dimension size) with (nm nanometer) same ((laser electron) with beam) and ((organic near2 molecular) (micro adj scale) (nano adj scale))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:02
S109	375	S108 and ("50" "100" "25" "75" "125" "150") with (nanometer nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:03
S110	19	S108 and ("50" "100" "25" "75" "125" "150") with (nanometer nm) same (electron with etch \$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:04

S111	2	S67 and electron with beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:22
S112	2	S67 and etch\$4 with pattern\$4 same (laser electron beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:26
S113	2	S67 and (lift "lift off")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 13:26
S114	3	"20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:36
S115	3	S114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:36
S116	3	S115 and (photo etch\$4) with (remov\$4 sacrific\$9 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:41
S117	2	S115 and electron with beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:46
S118	2	S115 and polymer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:46
S119	0	S115 and polymer with etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:46
S120	2	S115 and polymer same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:47
S121	0	S115 and polymer same etch\$4 and beam near3 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:47

S122	0	S115 and polymer same etch\$4 and beam with etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:47
S123	2	S115 and polymer same etch\$4 same pattern\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 10:49
S124	3	S115 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:04
S125	281	(etch\$4 with electron adj beam) same (pattern\$4 width dimension) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:05
S126	45	(etch\$4 with electron adj beam) same line with (pattern\$4 width dimension) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:07
S127	3	S115 and (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:08
S128	0	S115 and (beam with etch\$4 with (nm nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:09
S129	0	S115 and (beam with etch\$4 same (nm nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:09
S130	2	S115 and (beam same etch\$4 same (nm nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:13
S131	0	S115 and (beam with etch\$4) and (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:14
S132	45	S126 and (beam with etch\$4) and (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:14

S133	37	S126 and (beam with etch\$4) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:14
S134	36	S126 and (electron with beam with etch\$4) with (nm nanometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:15
S135	1	S126 and (electron with beam with etch\$4) with (nm nanometer) same polymer\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:37
S136	0	S126 and ((electron beam) with etch\$4) same (nm nanometer) same polymer\$4 not S135	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:17
S137	0	S126 and (electron beam) same (etch\$4 with (nm nanometer)) same polymer\$4 not S135	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:17
S138	1	S126 and (electron beam) same (etch\$4 same (nm nanometer)) same polymer\$4 not S135	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:18
S139	59	(electron beam) with (etch\$4 with (nm nanometer)) with polymer\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:19
S140	10	(electron with beam) with (etch\$4 with (nm nanometer)) with polymer\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:29
S141	2	S115 and adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:30
S142	0	S115 and adsorb\$4 same (immers\$5 solut\$4 solvent dissolv\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:31
S143	670	organic with molecu\$5 with adsorb\$4 with (immers\$5 solut\$4 solvent dissolv\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:31

S144	11	S143 and (electron with beam with (etch\$4 pattern\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:32
S145	1	S135 and etch\$4 near\$5 ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:38
S146	1	S135 and ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:39
S147	1	S135 and (differ\$5 near\$5 etch \$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:44
S148	1	S135 and adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:44
S149	1	S135 and adsorb\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:45
S150	2	"20050051768"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:45
S151	2	S150 and adsorb\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:46
S152	1	S150 and adsorb\$9 with (dissolv \$4 immers\$5 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:48
S153	0	S115 and adsorb\$9 with (dissolv \$4 immers\$5 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:49
S154	2	S115 and (dissolv\$4 immers\$5 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:58

S155	9	("5275851" "5277068" "5587128" "6013565" "6034414" "6074725" "6136212" "6180536" "6239451").PN. OR ("7052616"). URPN	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/02 11:49
S156	0	S155 and adsor\$9 with (dissolv \$4 immers\$5 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:50
S157	1	S155 and adsor\$9 same (dissolv \$4 immers\$5 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:50
S158	1150	216/2.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:58
S159	194	S158 and (electron with beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 11:59
S160	96	S158 and (electron with beam with (pattern\$4 polymer\$4 line width expos\$5 sacrific\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 12:01
S161	4	S158 and (electron with beam with (pattern\$4 line width expos \$5 sacrific\$5) with polymer\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 12:01
S162	3	"20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 09:08
S163	3	S162	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 09:08
S164	2	S163 and (beam lithogra\$9)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 09:54
S165	1	("6034414").PN.	USPAT; USOCR	OR	OFF	2007/06/04 09:56
S166	1	("5277068").PN.	USPAT; USOCR	OR	OFF	2007/06/04 09:57

S167	2	S165 S166	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 09:57
S168	1	("7052616"). PN	USPAT; USOCR	OR	OFF	2007/06/04 09:58
S169	9	("5275851" "5277068" "5587128" "6013565" "6034414" "6074725" "6136212" "6180536" "6239451").PN. OR ("7052616"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 09:58
S170	1	S169 and beam same (nm nanometer "50" "100")	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 09:59
S171	0	S169 and beam same (nm nanometer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 09:59
S172	0	S169 and beam and (nm nanometer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:02
S173	2310	molecular adj scale	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:02
S174	14	S173 same beam with lithograph \$5	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:05
S175	0	S173 same beam with lithograph \$5 and (organic near3 molecular \$4)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:07
S176	10	S173 same beam with lithograph \$5 and organic	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/05 08:00
S177	10	S173 same beam with lithograph \$5 and organic and nm	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:15
S178	3	S173 same beam with lithograph \$5 and organic and (nm with beam)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:25
S179	1	"20030180627"	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:25
S180	1	S179 and "50"	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:31
S181	13	polymer near3 pattern\$5 with "50" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:30
S182	1	S179 and organic	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:35
S183	10	S176 and nm	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:43
S184	150	shamim.xp. and "216"/\$.ccor.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:44
S185	142	olsen.xp. and "216"/\$.ccor.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/04 10:44
S186	2312	molecular adj scale	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/05 08:00
S187	10	S186 same beam with lithograph \$5 and organic	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/05 08:00

S188	10	S187 and (nm nanometer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/01 12:43
S189	1	("5658698").PN.	USPAT; USOCR	OR	OFF	2007/09/01 12:43
S190	9	("5275851" "5277068" "5587128" "6013565" "6034414" "6074725" "6136212" "6180536" "6239451").PN. OR ("7052616"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 10:46
S191	1	S190 and (etch\$4 with (different differing differ difference various alternat\$5 ratio select\$4))	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 11:20
S192	5	S190 and (etch\$4 with (sacrific \$5 layer pattern))	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 10:51
S198	1	S190 and (nanometer nm)	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 10:54
S199	3	"20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 10:58
S200	3	S199	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:34
S201	3	S200 and (nano\$6 nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:25
S202	3	S200 and sacrific\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:04
S203	2	S200 and sacrific\$9 with thick\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:05
S204	2	S200 and sacrific\$9 with thick\$4 with (nm nano\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:06
S205	2	S200 and adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:06

S209	74	organic adj molecule with adsorb\$4 with (immers\$5 solut\$4 dissolv\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:50
S210	74	adsorb\$4 with organic adj molecule with adsorb\$4 with (immers\$5 solut\$4 dissolv\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:46
S211	3	organic adj molecule with adsorb\$4 with (immers\$5 solut\$4 dissolv\$4) with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:12
S212	4	organic adj molecule with adsorb\$4 with (immers\$5 solut\$4 dissolv\$4) same adsorb\$4 with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:13
S213	2	S200 and (etch\$4 with (different differing differ difference various alternat\$5 ratio select\$4))	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 11:21
S214	2	S200 and (etch\$4 lithogra\$9) with (different differing differ difference various)	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/05 11:22
S215	2	S200 and sacrific\$9 with (nm nano\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:25
S216	1	S209 same current with (sens\$4 detect\$4 monitor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:46
S217	7	S209 same (sens\$4 detect\$4 monitor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:48
S218	2	S209 same (sens\$4 detect\$4 monitor\$4) with electr\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:49
S219	9	organic adj molecule with adsorb\$4 same (sens\$4 detect\$4 monitor\$4) with electr\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:56
S220	1	("5497000").PN.	USPAT; USOCR	OR	OFF	2007/09/05 11:56

S221	5	"20030180627" "20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:56
S222	6	S220 S221	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:56
S225	29	S209 and (stir\$5 heat\$4) with solut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 11:59
S226	2	S209 and (stir\$5 heat\$4) with solut\$3 with adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:00
S227	5	S209 and (stir\$5 heat\$4) with adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:02
S228	1	organic adj3 molecule with stir\$5 with adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:03
S229	2	organic adj3 molecule with stir \$5 with adsorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:04
S230	944	438/99.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:04
S232	121	S230 and stir\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:04
S234	25	S230 and stir\$4 with (molecul\$4 dissolv\$4 immers\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:06
S235	1	S230 and stir\$4 with molecul\$4 with (dissolv\$4 immers\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:07

S236	5	S230 and stir\$4 with (dissolv\$4 immers\$5) and adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:08
S237	5	S230 and (stir\$4 agit\$4) with (dissolv\$4 immers\$5) and adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:08
S238	13	S230 and (stir\$4 agit\$4 mixing mixed mix) with (dissolv\$4 immers\$5) and adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:09
S241	9	"438"/\$.cols. and (stir\$4 agit\$4 mixing mixed mix) with (dissolv\$4 immers\$5) with adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:27
S242	7	((organic near molecular) (organic near semiconduct\$4)) and (stir\$4 agit\$4 mixing mixed mix) with (dissolv\$4 immers\$5) with adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:22
S243	1	((organic near molecular) (organic near semiconduct\$4)) same (stir\$4 agit\$4 mixing mixed mix) with (dissolv\$4 immers\$5) with adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:22
S245	2	"438"/\$.cols. and heat\$3 near solution with adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:28
S246	3	S200 and electric adj field	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:36
S247	2	S200 and passivat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:36
S248	389	adsor\$5 with (electric\$4 current) near2 (sens\$4 detect\$4 monitor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:47
S249	24	S248 and ((conductive organic) near2 molecule)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:48

S250	4	S248 and ((conductive organic) near2 molecule) with adsor\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:49
S251	43	S248 same molecule with adsor \$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 12:50
S252	2	S248 same molecule with adsor \$5 with (dissolv\$4 solut\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 13:29
S253	1	("5656698").PN.	USPAT; USOCR	OR	OFF	2007/09/05 13:29
S254	1	S253 and (nm nano\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/05 13:29
S255	1	("5497000").PN.	USPAT; USOCR	OR	OFF	2008/02/09 10:23
S256	5	"20030180627" "20030040173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 10:23
S257	6	S255 S256	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 10:23
S258	2	"20020134426"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 10:24
S259	1	("6770190").PN.	USPAT; USOCR	OR	OFF	2008/02/09 10:25
S260	9	S257 S258 S259	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 10:25
S261	1532	nano\$5 and (gap dimension) near3 (horizontal\$4 vertical\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:34

S262	6	nano adj gap and (gap dimension) near3 (horizontal\$4 vertical\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:35
S263	29	nano adj gap and (gap dimension) near3 (wide\$2 width deep\$4 depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:49
S264	17	nano adj gap same (gap dimension) near3 (wide\$2 width deep\$4 depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:49
S265	14	S264 not S262	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:49
S266	11	S264 not S262 and beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:55
S267	3	S265 not S266	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 11:56
S268	9	S266 and b	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 12:02
S269	3	S266 and effective with width with height	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 12:10
S270	5	S260 and (ti pt au)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/09 13:29

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